

DISTRIBUTED FEEDBACK AND DISTRIBUTED BRAGG REFLECTOR SEMICONDUCTOR LASERS

ABSTRACT

A DFB laser structure comprising a planar, semiconductor material-based active region sandwiched between first and second confinement layers; and a grating structure formed in the active region; wherein grating regions of the grating structure having alternating refractive indices comprise portions of the active region and dielectric material-based regions respectively.

FIG. 5